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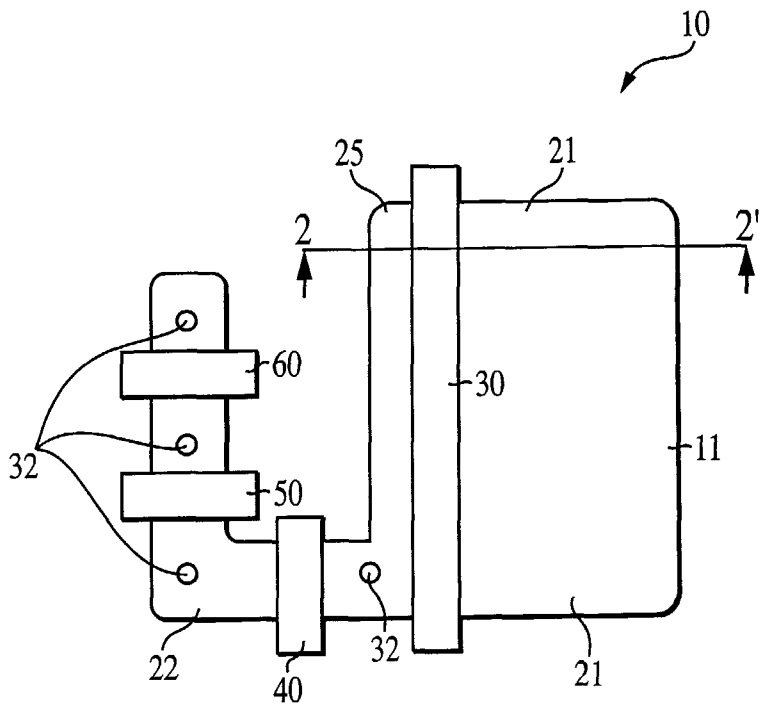
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(54) Title: ANGLED IMPLANT FOR TRENCH ISOLATION



(57) Abstract: A trench isolation having a sidewall and bottom implanted region located within a substrate of a first conductivity type is disclosed. The sidewall and bottom implanted region is formed by an angled implant, a 90 degree implant, or a combination of an angled implant and a 90 degree implant, of dopants of the first conductivity type. The sidewall and bottom implanted region located adjacent the trench isolation reduces surface leakage and dark current.

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